

TYANSHINE 广州市添鑫光电有限公司
Guangzhou Tianxin Photoelectric Co., Ltd

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High Power LED chip

High Power

UV

High Power LED chip

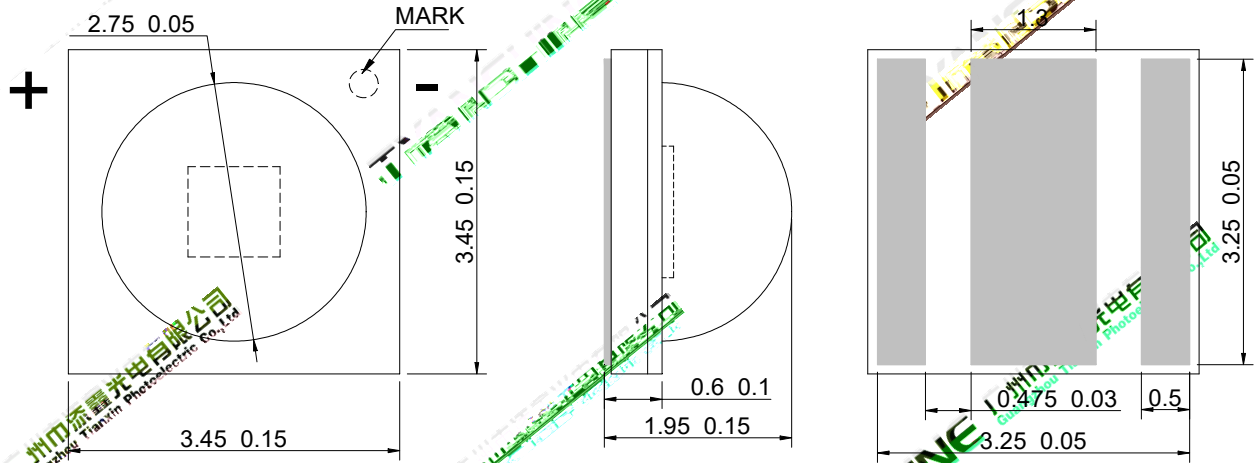
GaN

Red

High Power

High Power

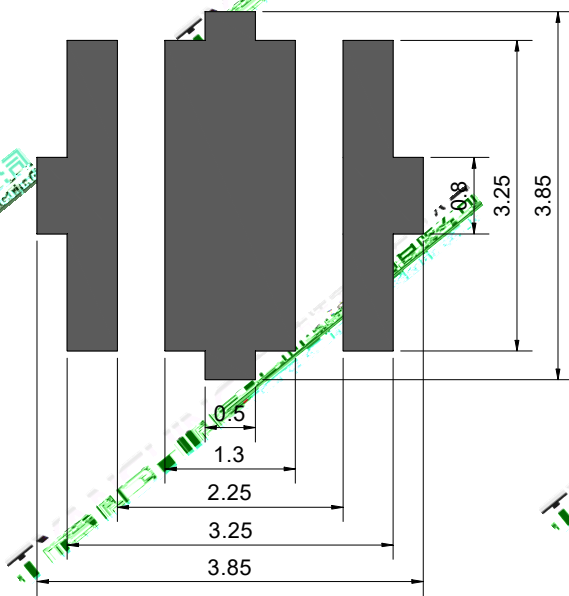
High Power



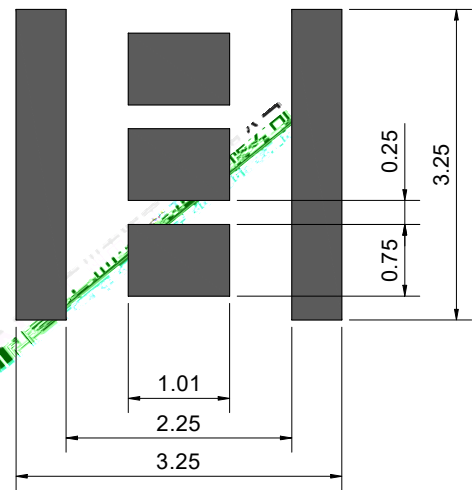
T ie

Side ie

B ie



Rec e ded lde ad



Rec e ded e cil a e

1. All dimensions are in millimeters.
2. Tolerance is indicated as ± 0.1.

Forward Current	IF	2000	mA
Reverse Voltage	VR	Not defined	V
Power Dissipation	PD	7.0	W
Junction Temperature	Tj	150	°C
Electrostatic Discharge Threshold (ESD)	ESD	ESD level	V
Storage Temperature	Tg	-40 ~ +70	°C
Operating Temperature	T	-40 ~ +85	°C

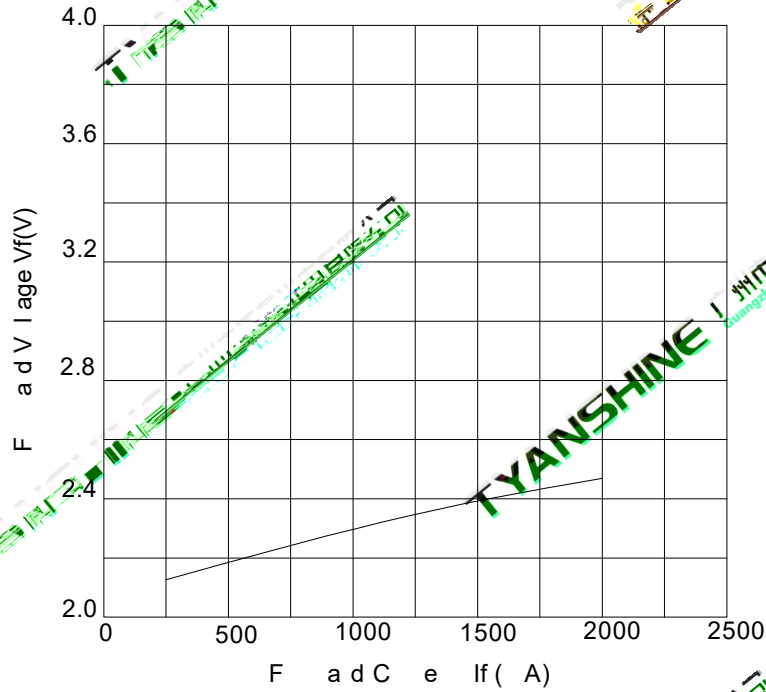
1. Specific anti-static discharge protection.
2. The data sheet specifies the failure rate. The actual data is subject to the manufacturer's acknowledgment.
3. Precautions for ESD:
STATIC SHIELD Electrostatic discharge protection for LED. It is recommended to use anti-static gloves when handling the LED. All devices, especially the sensitive components, should be stored in a static-free environment.

Li Fl		If=1000 A	150	190	210	l
F ad V lage	V		2.3	2.5	2.8	V
Vie i gA gle a 50 IV	2 1/2			120		Deg
Peak E i i Wa ele gh			620	625	630	
D ia Wa ele gh	d		615	619	625	
Vie i gA gle a 50 IV	2 1/2		12	16	20	
Re e eC e	I _R					A
Ne al Re i a ce J ci Ca e	R _{ce}	If=1000 A		4.9		K/W
Te e a eC efficie f V lage	V F/T			-2		V/

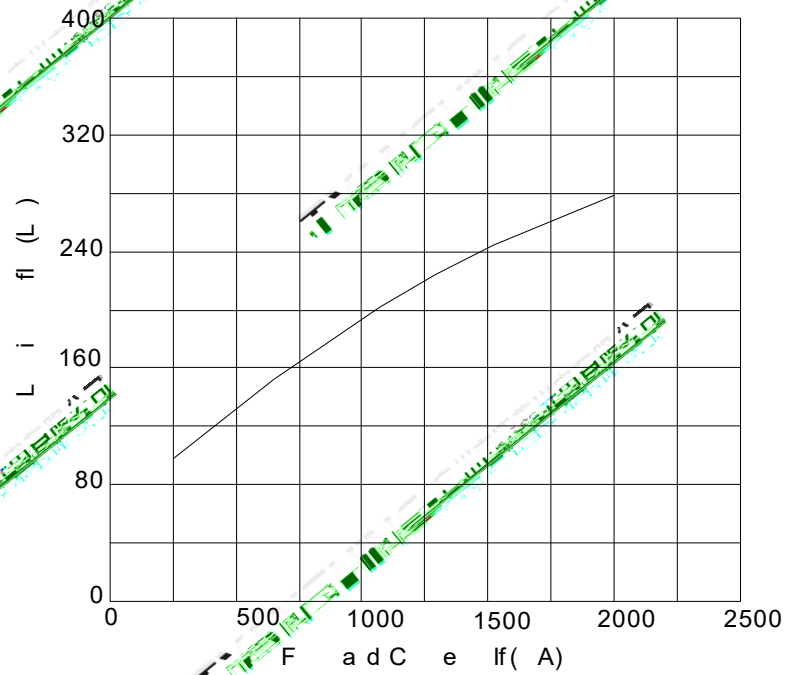
1. Li i e i i ea ed i h a ligh e a d file c bi ai ha a i a e he CIE e e- e e c e.
2. 1/2 i he ff- a i a gle a hich he l i i e i i half he a i a l i i e i .
3. Li fl ea e e le a ce: 15%.
4. F a d lage ea e e le a ce: 0.15V.

(25 A bie Te ea eU le Ohe i eN ed)

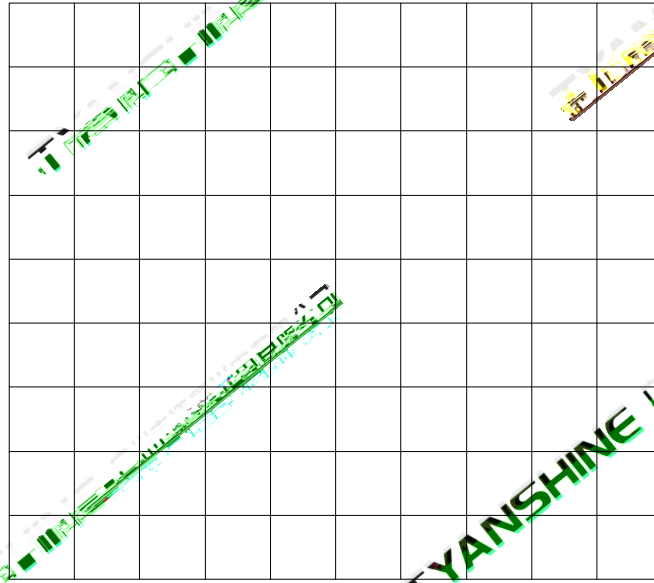
F adC e VS. F adV lage



F adC e VS. L i fl



Te e a e VS. F u l a d V l a g e (IF=1000 A)



Temperature: 5 30 (41 86)

Humidity: 60% RH Max.

Use the circuit in the figure.

